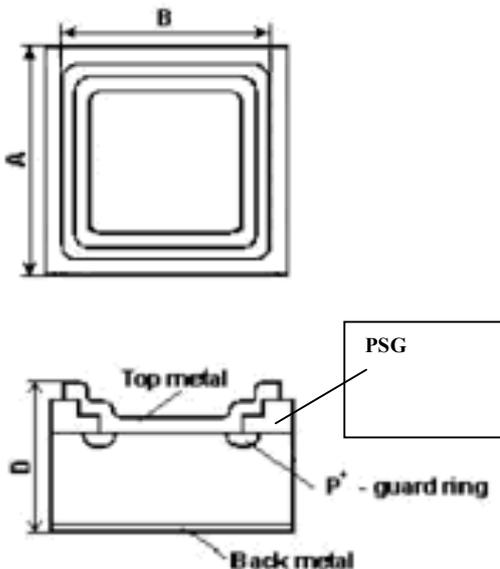


SCHOTTKY DIODES. KDS-03040H

PRELIMINARY

Aug.2012

 VSP-MIKRON	3A/40V. Die Size-60mil.			
Electrical Characteristics	Symbol	Unit	Spec. limit	Die Sort
Breakdown Voltage @ $I_R=10mA$	V_B	V	40	45
Average Rectified Forward Current	$I_{F(AV)}$	A	3,0	-
DC Forward Voltage @ 25°C, $I_F=3,0A$	V_F	V	0,42	0,40
Maximum Reverse Current @ 25°C, $V_R=45V$ @ 25°C, $V_R=40V$ @ 100°C, $V_R=40V$	I_R	MA	- 0,70 50,0	0,70 0,50 45,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	I_{FSM}	A	90	
Peak Repetitive Reverse Surge Current @ 2,0µs, $f=1kHz.$, $T_J<150°C.$	I_{RRM}	A	2,0	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	ESD	kV	±8 (contact)	
Voltage Rate of Change	dV/dt	V/µS	10.000	
Operating Junction Temperature	T_J	°C	125	



DIM	ITEM	µm
A_x A_y	Die Size	1520 1520
B_x B_y	Top Metal Size	1380 1380
D	Thickness	300max.
Scribe line Width		80

Top metal: a) **Al** – for Wire Bonding;
b) **Al-Ni-Ag** – for Soldering.

Backside metal: **Ti-Ni-Ag.**